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June 2014



**FQA70N10** 

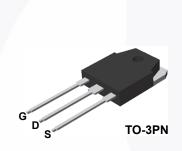
## N-Channel QFET<sup>®</sup> MOSFET 100 V, 70 A, 23 mΩ

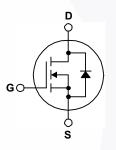
## Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### Features

- 70 A, 100 V, R\_{DS(on)} = 23 m\Omega (Max) @V\_{GS} = 10 V, I\_D = 35 A
- Low Gate Charge (Typ. 85 nC)
- Low Crss (Typ. 150 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





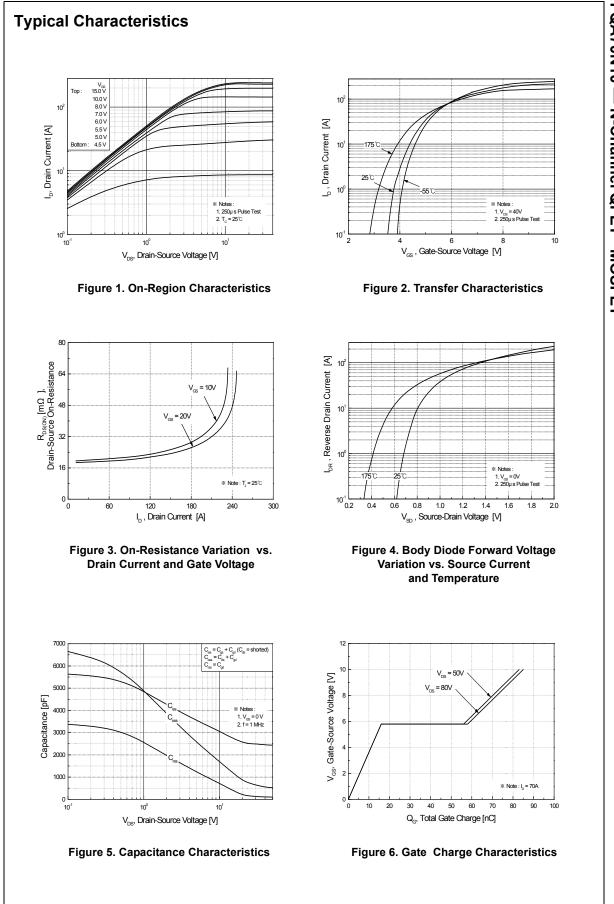
#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted

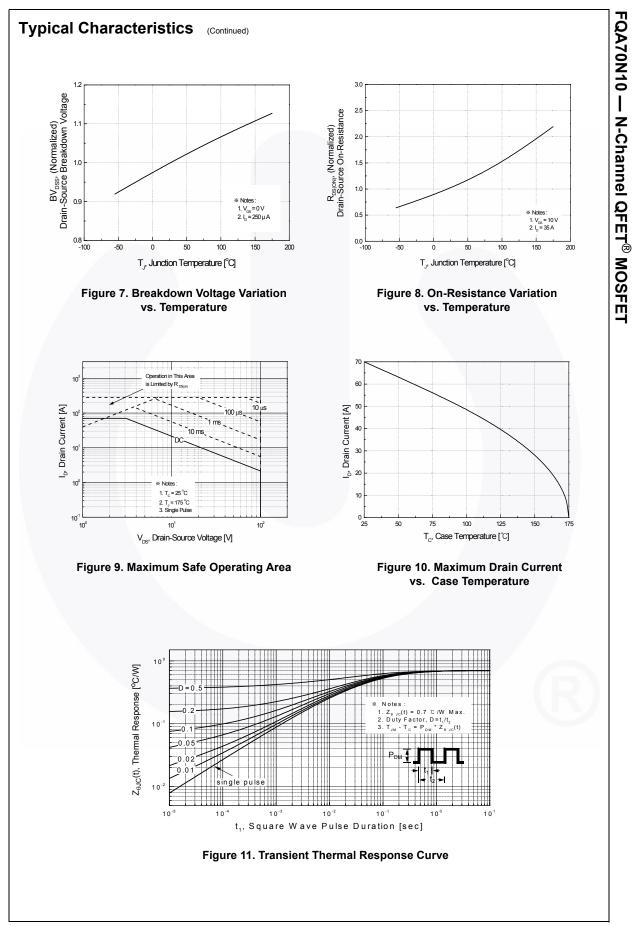
Symbol	Parameter		FQA70N10	Unit
V <sub>DSS</sub>	Drain-Source Voltage		100	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )		70	A
	- Continuous (T <sub>C</sub> = 1	100°C)	49.5	A
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	280	А
V <sub>GSS</sub>	Gate-Source Voltage		± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		1300	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	70	А
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	21.4	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C		214	W
			1.43	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

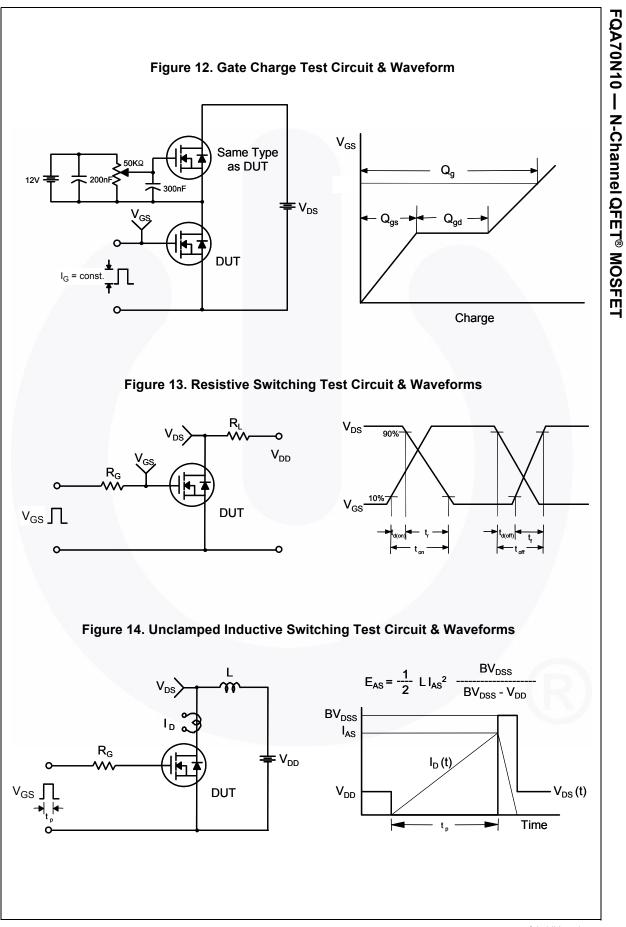
## **Thermal Characteristics**

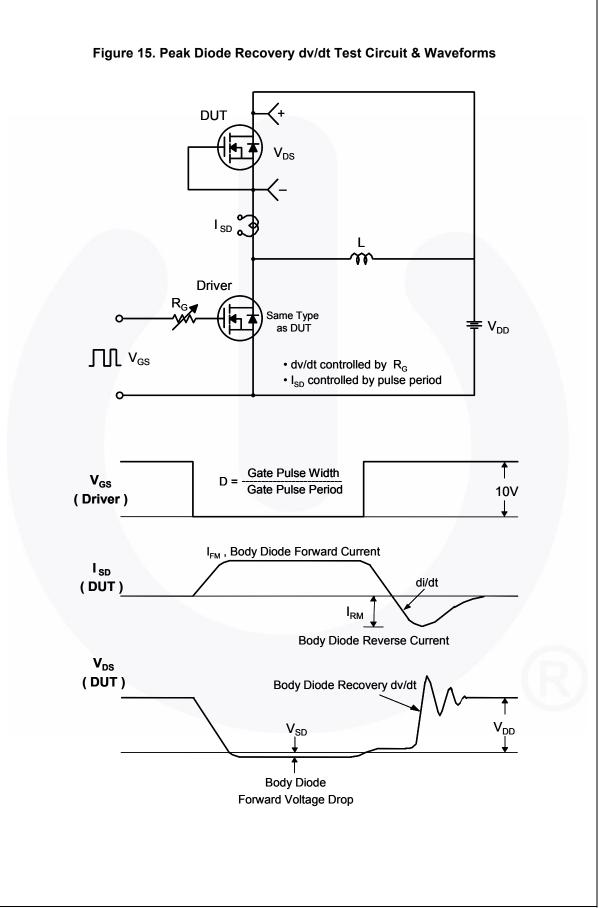
Symbol	Parameter	FQA70N10	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.7	°C/W	
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

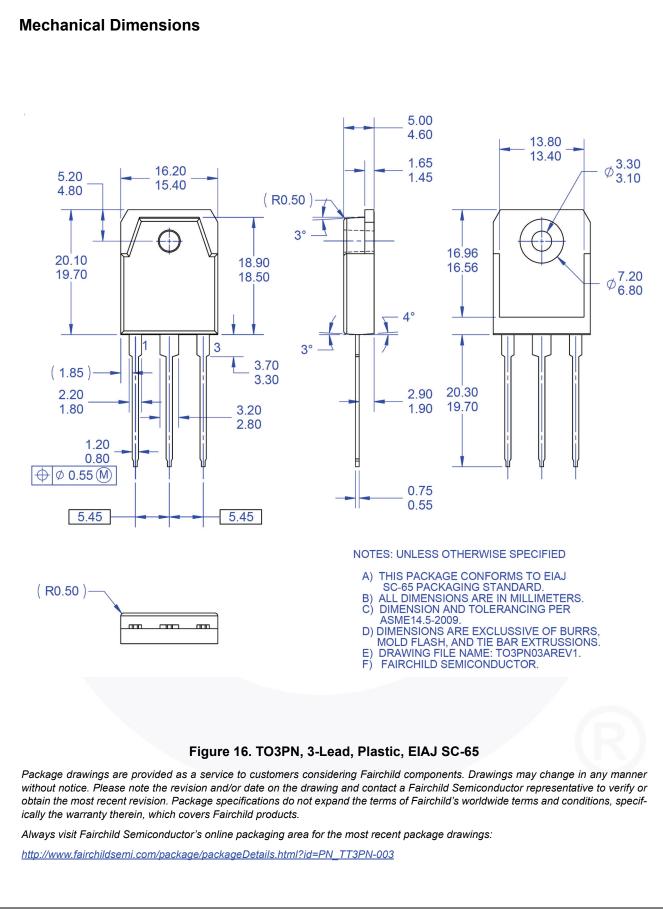
Device MarkingDeviceFQA70N10FQA70N10		Device	Package	Reel Size		Tape Wi	dth	Quantity
		TO-3PN -			-		30	
lectri	cal Char	racteristics T <sub>c</sub> = 25°C	C unless otherwise noted					
Symbol		Parameter	Test Condition	IS	Min	Тур	Мах	Unit
BV <sub>DSS</sub>	prain-Sou		V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		100			V
ABV <sub>DSS</sub>	Drain-Source Breakdown Voltage Breakdown Voltage Temperature				100			v
$\Delta T_{\rm J}$	Coefficient		$I_D = 250 \ \mu A$ , Referenced to $25^{\circ}C$			0.1		V/°C
I <sub>DSS</sub>	Zoro Cato	Voltago Drain Curront	$V_{DS}$ = 100 V, $V_{GS}$ = 0 V				1	μA
Zero Gate Voltage Drain Current		Vollage Drain Current	V <sub>DS</sub> = 80 V, T <sub>C</sub> = 150°C				10	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward		$V_{GS}$ = 25 V, $V_{DS}$ = 0 V			100	nA	
GSSR	Gate-Body	Leakage Current, Reverse	$V_{GS}$ = -25 V, $V_{DS}$ = 0 V	_			-100	nA
On Cha	racteristi	cs						
V <sub>GS(th)</sub>	Gate Three	shold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0		4.0	V
R <sub>DS(on)</sub>	Static Drai On-Resista		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 35 A			0.019	0.023	Ω
9 <sub>FS</sub>	Forward T	ransconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 35 A			48		S
C <sub>iss</sub>	ic Charac Input Capa	acitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,			2500	3300	pF
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capa Output Ca Reverse T	acitance pacitance ransfer Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz			2500 720 150	3300 940 200	pF pF pF
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi	Input Capa Output Ca Reverse T ing Chara	acitance pacitance ransfer Capacitance acteristics				720 150	940 200	pF pF
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi	Input Capa Output Cap Reverse Tr ing Chara Turn-On D	acitance pacitance ransfer Capacitance Incteristics elay Time				720 150 30	940 200 70	pF pF ns
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi	Input Capa Output Ca Reverse T ing Chara Turn-On D Turn-On R	acitance pacitance ransfer Capacitance cap	f = 1.0 MHz			720 150 30 470	940 200 70 950	pF pF ns ns
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi t <sub>d</sub> (on) t <sub>r</sub> t <sub>d</sub> (off)	Input Capa Output Ca Reverse T <b>ing Chara</b> Turn-On D Turn-On R Turn-Off D	acitance pacitance ransfer Capacitance capacitance ransfer Capacitance capacit	f = 1.0 MHz V <sub>DD</sub> = 50 V, I <sub>D</sub> = 70 A,	(Note 4)	  	720 150 30 470 130	940 200 70 950 270	pF pF ns ns ns
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> <b>Switch</b> i t <sub>d</sub> (on) t <sub>r</sub> t <sub>d</sub> (off) t <sub>f</sub>	Input Capa Output Cap Reverse T ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F	acitance pacitance ransfer Capacitance cap	f = 1.0 MHz V <sub>DD</sub> = 50 V, I <sub>D</sub> = 70 A, R <sub>G</sub> = 25 Ω	(Note 4)	   	720 150 30 470 130 160	940 200 70 950 270 330	pF pF ns ns ns ns
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> <b>Switchi</b> t <sub>d</sub> (on) t <sub>r</sub> t <sub>d</sub> (off) t <sub>f</sub> Q <sub>g</sub>	Input Capa Output Ca Reverse Ti <b>ng Chara</b> Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate	acitance pacitance pacitance ransfer Capacitance capac	f = 1.0 MHz $V_{DD} = 50 \text{ V}, \text{ I}_{D} = 70 \text{ A},$ $R_{G} = 25 \Omega$ $V_{DS} = 80 \text{ V}, \text{ I}_{D} = 70 \text{ A},$	(Note 4)	    	720 150 30 470 130 160 85	940 200 70 950 270 330 110	pF pF ns ns ns ns nc
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> <b>Switchi</b> t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Q <sub>g</sub> Q <sub>gs</sub>	Input Capa Output Ca Reverse T ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour	acitance pacitance pacitance pacitance capacitance cap	f = 1.0 MHz V <sub>DD</sub> = 50 V, I <sub>D</sub> = 70 A, R <sub>G</sub> = 25 Ω	(Note 4)	  	720 150 30 470 130 160 85 16	940 200 70 950 270 330 110 	pF pF ns ns ns nc nC
$\begin{array}{c} C_{iss} \\ C_{oss} \\ C_{rss} \end{array}$	Input Capa Output Ca Reverse T ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drair	acitance pacitance pacitance pacitance capacitance cap	f = 1.0 MHz $V_{DD} = 50 V, I_D = 70 A,$ $R_G = 25 \Omega$ $V_{DS} = 80 V, I_D = 70 A,$ $V_{GS} = 10 V$	(Note 4)	     	720 150 30 470 130 160 85	940 200 70 950 270 330 110	pF pF ns ns ns ns nc
$\begin{array}{c} C_{iss} \\ C_{oss} \\ C_{rss} \end{array}$	Input Capa Output Capa Reverse T <b>ing Chara</b> Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drair	acitance pacitance ransfer Capacitance acteristics elay Time elay Time all Time Charge ce Charge n Charge	f = 1.0 MHz $V_{DD} = 50 V, I_D = 70 A,$ $R_G = 25 \Omega$ $V_{DS} = 80 V, I_D = 70 A,$ $V_{GS} = 10 V$	(Note 4)	     	720 150 30 470 130 160 85 16	940 200 70 950 270 330 110 	pF pF ns ns ns nc nC
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub> Switchi t <sub>d</sub> (on) t <sub>r</sub> t <sub>d</sub> (off) t <sub>f</sub> Q <sub>g</sub> Q <sub>g</sub> Q <sub>gd</sub> Drain-S	Input Capa Output Ca Reverse T ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drair Cource Dia	acitance pacitance pacitance ransfer Capacitance capac	$f = 1.0 \text{ MHz}$ $V_{DD} = 50 \text{ V}, I_D = 70 \text{ A},$ $R_G = 25 \Omega$ $V_{DS} = 80 \text{ V}, I_D = 70 \text{ A},$ $V_{GS} = 10 \text{ V}$ $MAXIMUM Rating the forward Current$ Forward Current	(Note 4)	     	720 150 30 470 130 160 85 16 42	940 200 70 950 270 330 110  	pF pF ns ns ns nc nC nC
Ciss Coss Crss Switchi dd(on) dr dd(off) dr Qg Qg Qg Qg Drain-S SM VSD	Input Capa Output Ca Reverse T ing Chara Turn-On D Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drair Cource Did Maximum Maximum Drain-Sour	acitance pacitance pacitance ransfer Capacitance ransfer Capacitan	$f = 1.0 \text{ MHz}$ $V_{DD} = 50 \text{ V}, I_D = 70 \text{ A},$ $R_G = 25 \Omega$ $V_{DS} = 80 \text{ V}, I_D = 70 \text{ A},$ $V_{GS} = 10 \text{ V}$ $N \text{ Maximum Rating}$ $D \text{ ode Forward Current}$ $T \text{ Forward Current}$ $V_{GS} = 0 \text{ V}, I_S = 70 \text{ A}$	(Note 4)	        	720 150 30 470 130 160 85 16 42	940 200 70 950 270 330 110   70	pF pF ns ns ns nC nC nC A
Ciss Coss Crss Switchi d(on) tr d(off) tr Qg Qg Qg Qgd Drain-S	Input Capa Output Ca Reverse T ing Chara Turn-On D Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drair Cource Did Maximum Maximum Drain-Sour	acitance pacitance ransfer Capacitance acteristics elay Time elay Time all Time Charge ce Charge o Charge o Charge De Characteristics and Continuous Drain-Source Dide Pulsed Drain-Source Dide F	f = 1.0 MHz $V_{DD} = 50 V, I_D = 70 A,$ $R_G = 25 \Omega$ $V_{DS} = 80 V, I_D = 70 A,$ $V_{GS} = 10 V$ <b>nd Maximum Rating</b> pde Forward Current Forward Current	(Note 4)	      	720 150 30 470 130 160 85 16 42	940 200 70 950 270 330 110   70 280	pF pF ns ns ns nC nC nC A A

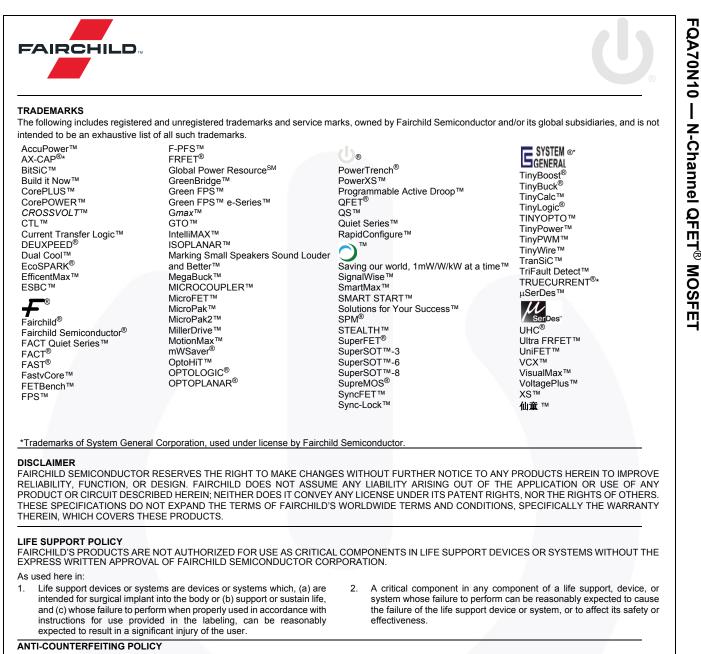












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